

## NDSH50120C

# Silicon Carbide Schottky Diode, 1200V, 50A, TO-247-2LD

### Product Overview

For complete documentation, see the data sheet.

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability to silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### Features

- Max Junction Temperature
- Avalanche Rated
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

#### Benefits

- $T_j = 175\text{ }^\circ\text{C}$
- 380 mJ



#### Applications

- SMPS
- Solar
- Industrial Power
- PFC

#### End Products

- UPS
- Solar Inverter

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Family	Configuration	$V_{RRM}$ (V)	$I_{F(ave)}$ (A)	$V_F$ (Max)	$I_{FSM}$ (A)	$I_R$ (Max) ( $\mu\text{A}$ )	Package Type
NDSH50120C	9.0319	 	Active	D3	Single	1200	50	1.75	231	200	TO-247-2LD